

Common recipe etch rate values in Oxford etcher

Recipe	N-Al2O3 _ All_Half	O - Al Etch __25C	O - HfO2_etch	O-SiNx_Etch	O-SiO2_Etch_(PR_Mask)	N-ZnO _Etch	O - SiO2 RIE Mode
Film							
Si	3043	2100	1900	14800	1300	2700	- 400?
SiO2	832	368	1548	2058	1134	2576	460
Nit	485	1342	1093	8351	1559	3522	449
LSN	543	999	1030	4043	1533	1910	884
Resist	843	4188	1570	5478	1567	3047	100
Poly Silicon							
PECVD Oxide	963			2920			
PECVD Nit							
Al2O3	685	487	1308	295	460	584	42
HfO2	678	698	1360	231	630	725	
ZnO	288	378	636	52	313	241	20
TiO2							
Al		3933					
Ti							
Nb							
Cr							

* With 10 min conditioning run, varies greatly (~300 Angstroms/min) from run to run

† The center of the wafer is etched ~200 Angstroms/min faster than the rest of the wafer

All values listed are in Angstroms / min. These values are a guide only.

To get best results confirm etch rate for your sample yourself.

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